L	Hits	Search Text	DB	Time stamp
Number			<u> </u>	
1	77206	semic ndu t radj waf r	USPAT;	2002/05/31
			US-P PUB;	11:13
			EPO; JPO;	
			DERWENT;	
_			IBM_TDB	
2	30	(semiconductor adj wafer) and barcode	USPAT;	2002/05/31
			US-PGPUB;	11:18
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
3	3401	(semiconductor adj wafer) and (bar code)	USPAT;	2002/05/31
			US-PGPUB;	11:18
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
4	362	(semiconductor adj wafer) and (bar adj	USPAT;	2002/05/31
		code)	US-PGPUB;	12:45
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
5	123	((semiconductor adj wafer) and (bar adj	USPAT;	2002/05/31
		code)) and mark	US-PGPUB;	12:45
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
6	0	((semiconductor adj wafer) and barcode)	USPAT;	2002/05/31
		and erase	US-PGPUB;	12:45
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
7	0	((semiconductor adj wafer) and barcode)	USPAT;	2002/05/31
		and efface	US-PGPUB;	12:45
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
8	1	((semiconductor adj wafer) and (bar adj	USPAT;	2002/05/31
		code)) and erase	US-PGPUB;	12:46
•			EPO; JPO;	,
			DERWENT;	g
			IBM_TDB	
9	0	((semiconductor adj wafer) and (bar adj	USPAT;	2002/05/31
:		code)) and efface	US-PGPUB;	13:34
		··· .	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
10	2	6268641.pn.	USPAT;	2002/05/31
		•	US-PGPUB;	16:00
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	

11	2	6312876.pn.	USPAT;	2002/05/31
			US-P PUB;	16:00
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
12	102	430/13.ccls.	USPAT;	2002/05/31
			US-PGPUB;	16:00
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
13	396	257/620.ccls.	USPAT;	2002/05/31
			US-PGPUB;	16:00
	1		EPO; JPO;	
			DERWENT;	
			IBM_TDB	

L	Hits	S arch Text	DB	Tim stamp
Number	1006	235/494.ccls.	USPAT;	2002/05/30
			US-PGPUB;	17:55
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	0	235/494.ccls. and chiba.in.	USPAT;	2002/05/30
•		200/404iccio. and cimbaini	US-PGPUB;	
			EPO; JPO;	17.00
			DERWENT;	
			IBM_TDB	
_	0	jp-223380-\$.did.	USPAT;	2002/05/30
-		)p-225500-\$.did.	US-PGPUB;	
			EPO; JPO;	17:50
			1 7	
			DERWENT;	
		112222011	IBM_TDB	2002/05/20
-	9	"223380"	USPAT;	2002/05/30
			US-PGPUB;	17:57
			EPO; JPO;	
			DERWENT;	
	_		IBM_TDB	
-	0	jp-223380-\$.did.	USPAT;	2002/05/30
			US-PGPUB;	17:58
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	0	jp-5923512-\$.did.	USPAT;	2002/05/30
			US-PGPUB;	17:58
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	2	jp-2000223380-\$.did.	USPAT;	2002/05/30
			US-PGPUB;	18:00
			EPO; JPO;	•
			DERWENT;	
			IBM_TDB	
-	0	jp-2175154-\$.did.	USPAT;	2002/05/30
			US-PGPUB;	18:00
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	1	jp-3116919-\$.did.	USPAT;	2002/05/30
			US-PGPUB;	18:00
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	15423	chiba.in.	USPAT;	2002/05/30
			US-PGPUB;	18:02
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	

	818	chiba.in. and semi nductor	USPAT;	2002/05/30
			US-P PUB;	18:02
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	58	(chiba.in. and semiconduct r) and mark	USPAT;	2002/05/30
		(companion and composition ), and many	US-PGPUB;	18:05
			EPO; JPO;	10.00
			DERWENT;	
			IBM_TDB	
	153	(chiba.in. and semiconductor) and wafer	USPAT;	2002/05/30
-	133	(Cilibaliii. aliu selliicolluuctor) aliu walei	US-PGPUB;	18:06
			EPO; JPO;	10:00
			1 '	
•			DERWENT;	
	83	235/404 calc and comic and control	IBM_TDB	2002/05/20
-	63	235/494.ccls. and semiconductor	USPAT;	2002/05/30
			US-PGPUB;	18:10
İ			EPO; JPO;	
			DERWENT;	
	_		IBM_TDB	
-	8	(235/494.ccls. and semiconductor) and	USPAT;	2002/05/30
		wafer	US-PGPUB;	18:06
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	34	(235/494.ccls. and semiconductor) and	USPAT;	2002/05/30
		mark	US-PGPUB;	18:15
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	2	6305677.pn.	USPAT;	2002/05/30
			US-PGPUB;	18:16
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	174	269/13.ccls.	USPAT;	2002/05/30
			US-PGPUB;	18:18
			EPO; JPO;	
	1		DERWENT;	
]			IBM_TDB	
-	81423	semiconductor adj2 wafer	USPAT;	2002/05/30
1		<u>-</u>	US-PGPUB;	18:19
			EPO; JPO;	
	1		DERWENT;	
			IBM_TDB	
-	4744	(semiconductor adj2 wafer) and mark	USPAT;	2002/05/30
		,	US-PGPUB;	18:19
	1		EPO; JPO;	
			DERWENT;	
			IBM_TDB	
L	1	1		L

	4500	((semicondu t r adj2 waf r) and mark) and	USPAT;	2002/05/30
		(semi onduct radj wafer)	US-P PUB;	18:20
		(com character and matter)	EPO; JPO;	
			DERWENT;	
	ľ		IBM_TDB	
_	61	(((semi nduct radj2 waf r) and mark) and	USPAT;	2002/05/30
-	"	(semiconductor adj wafer)) and reproduce	US-PGPUB;	18:26
		(semiconductor adj water), and reproduce	EPO; JPO;	10.20
			DERWENT;	
			IBM_TDB	
	22	semiconductor adj mark	USPAT;	2002/05/30
-		Semiconductor adjimark	US-PGPUB;	18:29
			EPO; JPO;	10.23
			DERWENT;	
			IBM_TDB	
	1602	355/53.ccls.	_	2002/05/30
·	1602	JJJ/JJ/GG 3	USPAT; US-PGPUB;	18:29
			1	10:29
			EPO; JPO;	
			DERWENT; IBM_TDB	
	1154	355/53.ccls. and semiconductor	_	2002/05/30
•	1154	333/33.ccis. and semiconductor	USPAT;	
			US-PGPUB;	18:29 
			EPO; JPO;	
			DERWENT;	
	1052	(3EE/E2 colo and comicandurates) and surface	IBM_TDB	2002/05/20
•	1052	(355/53.ccls. and semiconductor) and wafer	USPAT;	2002/05/30
			US-PGPUB;	18:29
			EPO; JPO; DERWENT;	
			IBM_TDB	
	415	((355/53.ccls. and semiconductor) and	USPAT;	2002/05/30
-	413	wafer) and mark	US-PGPUB;	18:30
		waici j aliu iliaik	EPO; JPO;	10:30
			DERWENT;	
_	8	(//355/53 pole and comissenductor) and	IBM_TDB	2002/05/20
•	•	(((355/53.ccls. and semiconductor) and wafer) and mark) and reproduce	USPAT; US-PGPUB;	2002/05/30
		water, and mark) and reproduce	· ·	18:32
			EPO; JPO;	
			DERWENT;	
	0	///355/53 pole and comiconductors and	IBM_TDB	2002/05/20
•		(((355/53.ccls. and semiconductor) and	USPAT;	2002/05/30
		wafer) and mark) and efface	US-PGPUB;	18:32
			EPO; JPO;	
			DERWENT;	
	_	(//255/52 and naminary/	IBM_TDB	2002/05/20
•	5	(((355/53.ccls. and semiconductor) and	USPAT;	2002/05/30
		wafer) and mark) and erase	US-PGPUB;	18:34
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	l

	0	///255/52 cals, and paminanductor) and	USPAT;	2002/05/30
-		(((355/53.ccls. and semiconductor) and waf r) and mark) and (reproduc adj ras d	US-P PUB;	18:35
			EPO; JPO;	10.33
		adj marks)	DERWENT;	
			1	
		///255/50 - 1	IBM_TDB	2002/05/20
•	0	((((355/53.c ls. and semicondu tor) and	USPAT;	2002/05/30
		wafer) and mark) and (reproduce erased	US-PGPUB;	18:35
		marks)) and efface	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	10	((((355/53.ccls. and semiconductor) and	USPAT;	2002/05/30
		wafer) and mark) and (reproduce erased	US-PGPUB;	18:35
		marks)) and notch	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	300	(((355/53.ccls. and semiconductor) and	USPAT;	2002/05/30
	ĺ	wafer) and mark) and (reproduce erased	US-PGPUB;	18:38
		marks)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	0	(((355/53.ccls. and semiconductor) and	USPAT;	2002/05/30
		wafer) and mark) and (reproduce near	US-PGPUB;	18:39
		erased near marks)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	0	(((355/53.ccls. and semiconductor) and	USPAT;	2002/05/30
		wafer) and mark) and (reproduce same	US-PGPUB;	18:39
		erased same marks)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	121	(((355/53.ccls. and semiconductor) and	USPAT;	2002/05/30
		wafer) and mark) and identical	US-PGPUB;	18:40
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	9	((((355/53.ccls. and semiconductor) and	USPAT;	2002/05/30
		wafer) and mark) and identical) and	US-PGPUB;	18:44
		reproduce\$2	EPO; JPO;	ļ
			DERWENT;	-
			IBM_TDB	
-	172	(((355/53.ccls. and semiconductor) and	USPAT;	2002/05/30
		wafer) and mark) and prevent	US-PGPUB;	18:44
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	3	((((355/53.ccls. and semiconductor) and	USPAT;	2002/05/30
		wafer) and mark) and prevent) and erase	US-PGPUB;	18:53
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
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	354	355/43. Is.	USPAT;	2002/05/30
-	354	355/43. IS.	US-P PUB;	18:53
			1	10:55
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	2222/22/22
-	84	355/43. cls. and semiconduct r	USPAT;	2002/05/30
			US-PGPUB;	18:53
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	71	(355/43.ccls. and semiconductor) and wafer	USPAT;	2002/05/30
			US-PGPUB;	18:53
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	1	(((355/43.ccls. and semiconductor) and	USPAT;	2002/05/30
		wafer) and mark) and erase	US-PGPUB;	18:54
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
	45	((355/43.ccls. and semiconductor) and	USPAT;	2002/05/30
		wafer) and mark	US-PGPUB;	18:58
		· · · · · · · · · · · · · · · · · · ·	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	25968	355/\$.ccls.	USPAT;	2002/05/30
		000/4100101	US-PGPUB;	18:58
			EPO; JPO;	10.00
			DERWENT;	
			IBM_TDB	
<u> </u>	2116	355/\$.ccls. and semiconductor	USPAT;	2002/05/30
-	2110	333/\$.ccis. and Semiconductor	US-PGPUB;	18:59
			EPO; JPO;	10.33
			DERWENT;	
	4.460	/355/\$ cole and namicanductory and water	IBM_TDB	2002/05/20
-	1469	(355/\$.ccls. and semiconductor) and wafer	USPAT;	2002/05/30
			US-PGPUB;	18:59
			EPO; JPO;	
			DERWENT;	
		(Interior and	IBM_TDB	
-	497	((355/\$.ccls. and semiconductor) and wafer)	USPAT;	2002/05/30
		and mark	US-PGPUB;	18:59
			EPO; JPO;	
			DERWENT;	
	_		IBM_TDB	
-	8	(((355/\$.ccls. and semiconductor) and	USPAT;	2002/05/30
		wafer) and mark) and erase	US-PGPUB;	18:59
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	

-	13	(((355/\$.ccls. and semiconduct r) and	USPAT;	2002/05/30
		waf r) and mark) and repr duc	US-PGPUB;	19:02
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
	1	((((355/\$. Is. and semicondu tor) and	USPAT;	2002/05/30
		wafer) and mark) and erase) and	US-PGPUB;	19:02
		((((355/\$.ccls. and semiconductor) and	EPO; JPO;	
		wafer) and mark) and reproduce)	DERWENT;	
			IBM_TDB	